



Bipolar PNP Bare Die – BTP6063

Part Description

The BTP6063 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -200V
- VCEO = -200V
- VEBO = -6V
- hFE = 60-280 @ VCE = -5V, IC = -0.2A
- VCE(Sat) = -0.5V @ IC = -0.5A, IB = -50mA
- fT = 130 MHz @ VCE = -5V, IE = 0A
- COBO = 20pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to TOSHIBA 2SA1013 or ROHM 2SB1236A

Die Size (Unawn)

1200µm X 1200µm, 47 Mils X 47 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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